N-Channel 30-V (D-S) MOSFET with Schottky Diode

MOSFET PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.0135 @ V_{GS} = 10 V	10
	0.020 @ V_{GS} = 4.5 V	8

SCHOTTKY PRODUCT SUMMARY		
V_{DS} (V)	Diode Forward Voltage V_{SD} (V)	I_F (A)
30	0.53 V @ 3.0 A	3.8

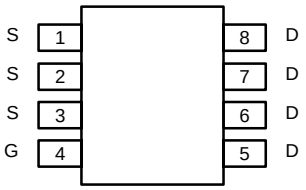
FEATURES

- TrenchFET® Power MOSFETS
- Fast Switching Speed
- Low Gate Charge

APPLICATIONS

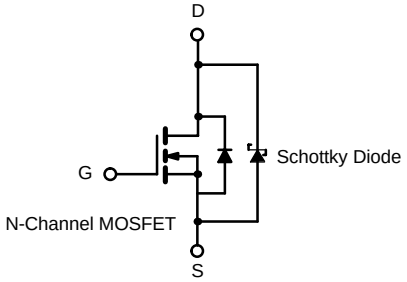
- DC-DC Logic Level
- Low Voltage and Battery Powered Applications

SO-8



Top View

Ordering Information:
Si4810BDY
Si4810BDY-T1 (with Tape and Reel)



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	10 sec	Steady State	Unit
Drain-Source Voltage (MOSFET)		V_{DS}	30		V
Reverse Voltage (Schottky)			30		
Gate-Source Voltage (MOSFET)		V_{GS}	±20		
Continuous Drain Current (T_J = 150°C) (MOSFET)[a]	T_A = 25°C	I_D	10	7.5	A
	T_A = 70°C		8	6	
Pulsed Drain Current (MOSFET)		I_{DM}	50		
Continuous Source Current (MOSFET Diode Conduction)[a]		I_S	2.3	1.25	
Average Foward Current (Schottky)		I_F	3.8	2.4	
Pulsed Foward Current (Schottky)		I_{FM}	40		
Maximum Power Dissipation (MOSFET)[a]	T_A = 25°C	P_D	2.5	1.38	W
	T_A = 70°C		1.6	0.88	
Maximum Power Dissipation (Schottky)[a]	T_A = 25°C		2.0	1.31	
	T_A = 70°C		1.3	0.84	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter	Device	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (t ≤ 10 sec)[a]	MOSFET	R_{thJA}	36	50	°C/W
	Schottky		44	60	
Maximum Junction-to-Ambient (t = steady state)[a]	MOSFET		73	90	
	Schottky		77	95	
Maximum Junction-to-Foot (t = steady state)[a]	MOSFET	R_{thJF}	17	21	
	Schottky		24	30	

Notes
a. Surface Mounted on FR4 Board.

For SPICE model information via the Worldwide Web: http://www.vishay.com/www/product/spice.htm

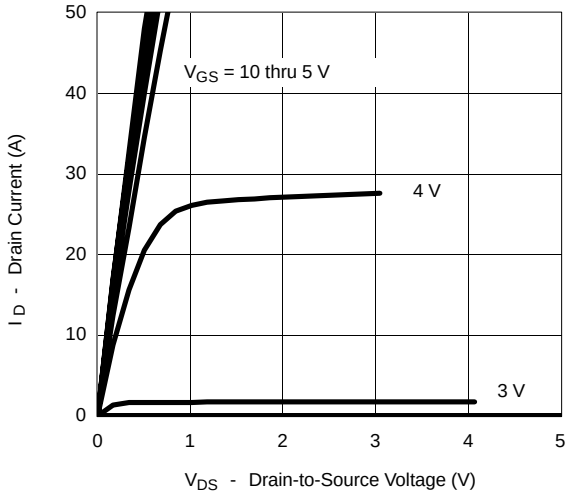
MOSFET + SCHOTTKY SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	1		3	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current (MOSFET + Schottky)	I_{DSS}	V_{DS} = 24 V, V_{GS} = 0 V		0.007	0.100	mA
		V_{DS} = 24 V, V_{GS} = 0 V, T_J = 100°C		1.5	10	
		V_{DS} = 24 V, V_{GS} = 0 V, T_J = 125°C		6.5	20	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 5 V, V_{GS} = 10 V	20			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 10 A		0.0105	0.0135	Ω
		V_{GS} = 4.5 V, I_D = 5 A		0.016	0.020	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 10 A		25		S
Schottky Diode Forward Voltage[a]	V_{SD}	I_S = 3.0 A, V_{GS} = 0 V		0.485	0.53	V
		I_S = 3.0 A, V_{GS} = 0 V, T_J = 125°C		0.420	0.47	
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = 15 V, V_{GS} = 5 V, I_D = 10 A		14.5	22	nC
Gate-Source Charge	Q_{gs}			6.3		
Gate-Drain Charge	Q_{gd}			4.7		
Gate Resistnce	R_G			0.55		Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 15 V, R_L = 15 Ω I_D ≅ 1 A, V_{GEN} = 10 V, R_G = 6 Ω		17	30	ns
Rise Time	t_r			13	20	
Turn-Off Delay Time	$t_{d(off)}$			45	90	
Fall Time	t_f			15	25	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 3.0 A, di/dt = 100 A/μs		36	70	

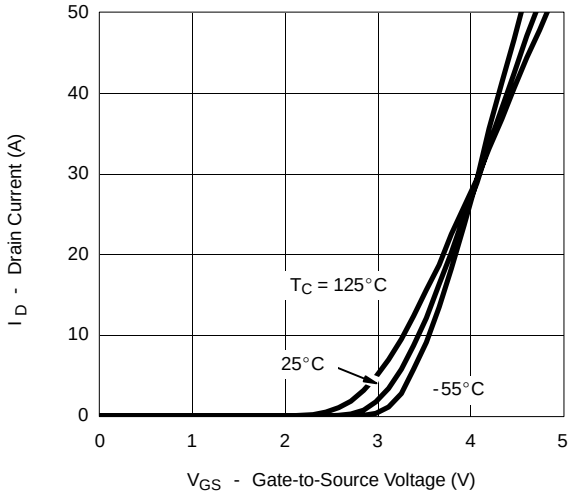
Notes
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

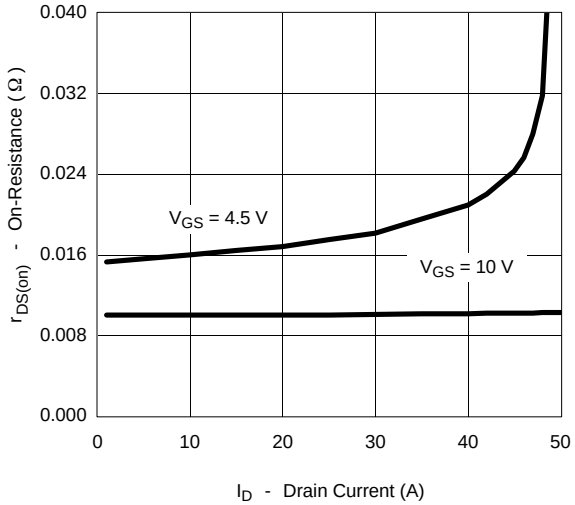
Output Characteristics



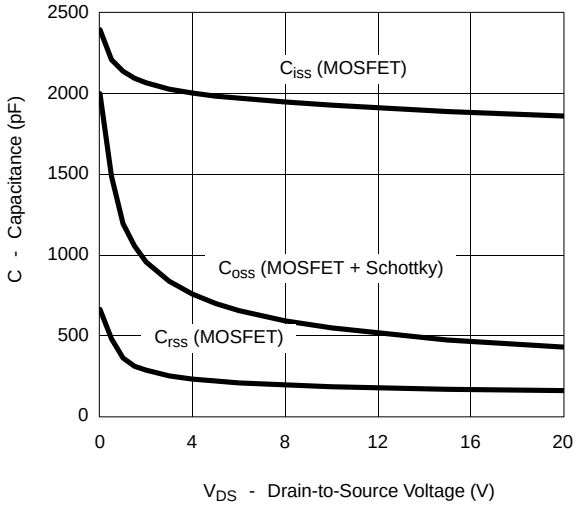
Transfer Characteristics



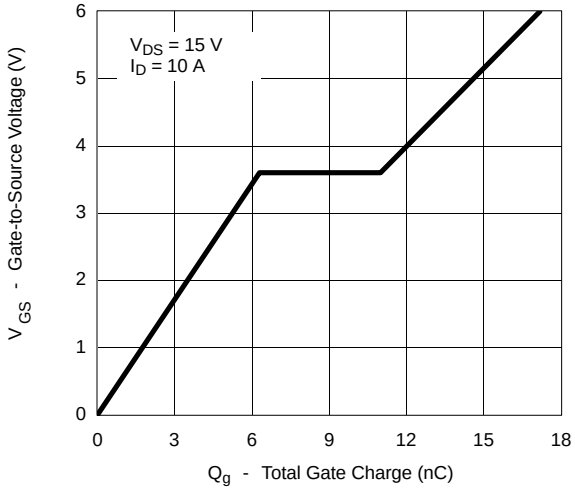
On-Resistance vs. Drain Current



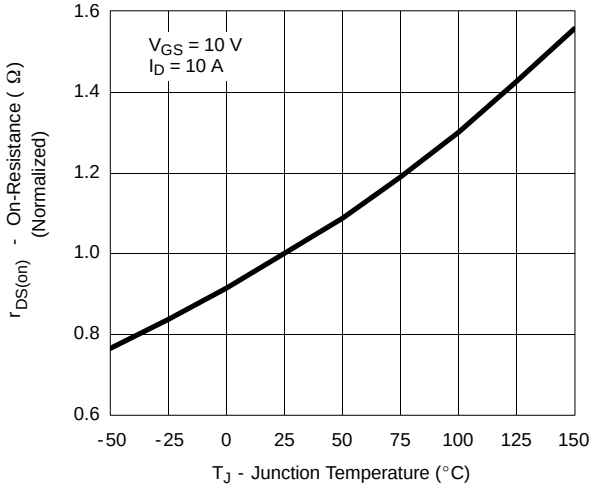
Capacitance



Gate Charge

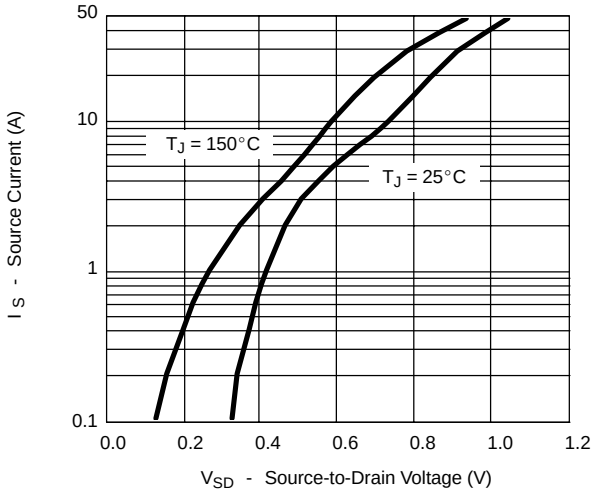


On-Resistance vs. Junction Temperature

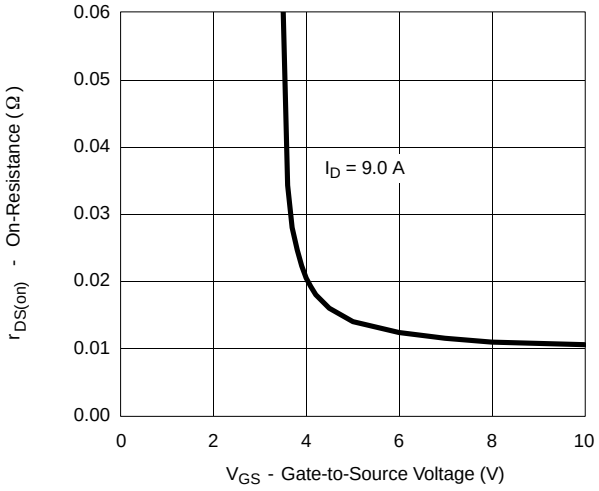


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

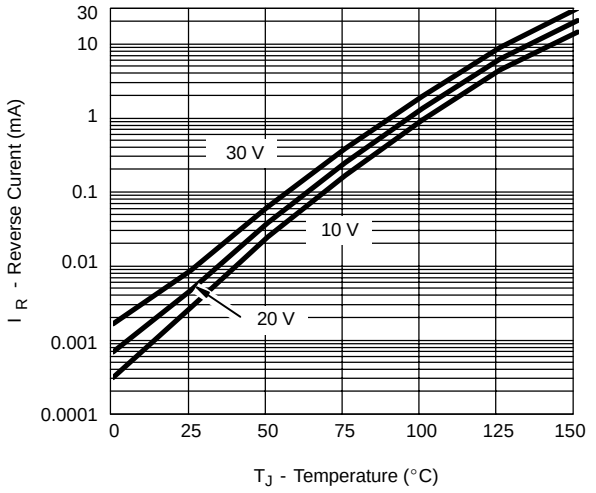
Source-Drain Diode Forward Voltage



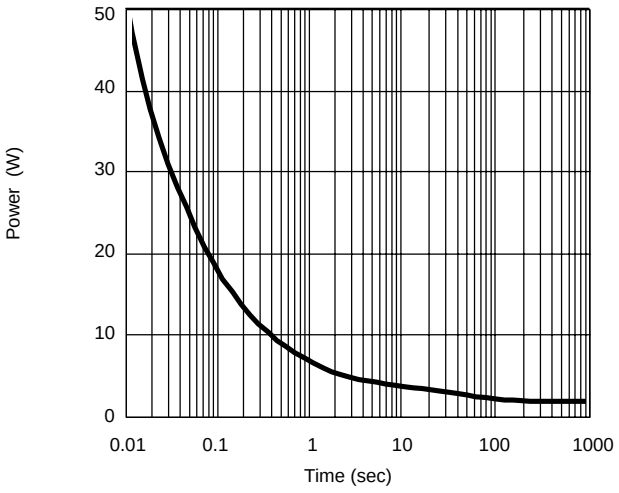
On-Resistance vs. Gate-to-Source Voltage



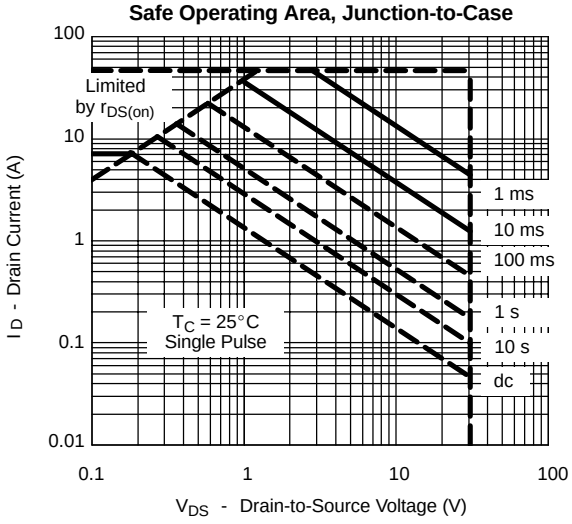
Reverse Current (Schottky)



Single Pulse Power

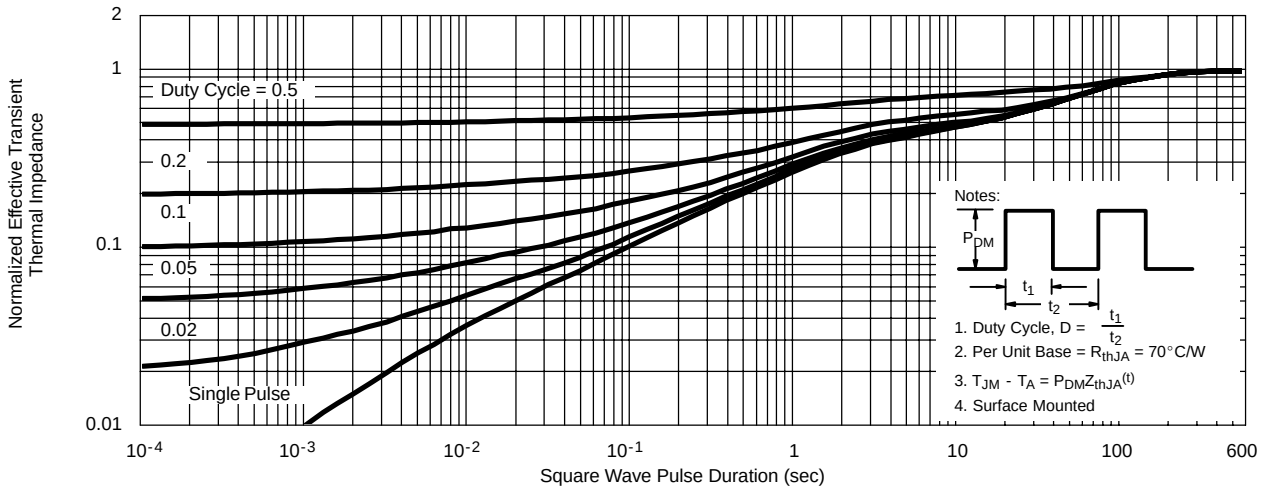


Safe Operating Area, Junction-to-Case



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot